Byeong Hyeon Lee

List of Publications by Year in descending order

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1684188 1281871 14 134 5 11 citations g-index h-index papers 16 16 16 95 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Electrical Performance of Amorphous Oxide/Colloidal Quantum Dot/Amorphous Oxide Hybrid Thin Film Transistor. Transactions on Electrical and Electronic Materials, 2022, 23, 25.	1.9	0
2	Ammonia Gas Sensing Properties of 6,13-Bis(tri-isopropylsilyethynyl) Pentacene Based Field-Effect Transistor. Transactions on Electrical and Electronic Materials, 2022, 23, 182-186.	1.9	3
3	Effect of Silicon Doping on the Electrical Performance of Amorphous SilnZnO Thin-film Transistors. Transactions on Electrical and Electronic Materials, 2021, 22, 133-139.	1.9	1
4	High Sensitivity of HCl Gas Sensor Based on Pentacene Organic Field-Effect Transistor. Transactions on Electrical and Electronic Materials, 2021, 22, 140-145.	1.9	3
5	Characteristics and Electronic Band Alignment of a Transparent p-Cul/n-SiZnSnO Heterojunction Diode with a High Rectification Ratio. Nanomaterials, 2021, 11, 1237.	4.1	6
6	Notice of Removal: Exceptionally Linear and Highly Sensitive Photo-Induced Unipolar Inverter Device. IEEE Journal of the Electron Devices Society, 2021, 9, 180-186.	2.1	4
7	Flexible artificial Si-In-Zn-O/ion gel synapse and its application to sensory-neuromorphic system for sign language translation. Science Advances, 2021, 7, eabg9450.	10.3	41
8	Mechanism of carrier controllability with metal capping layer on amorphous oxide SiZnSnO semiconductor. Scientific Reports, 2019, 9, 886.	3.3	22
9	Electrode-Adaptive Thin-Film Integrated Logic Circuits. IEEE Transactions on Electron Devices, 2019, 66, 957-962.	3.0	3
10	Investigation on the improvement of stability of nitrogen doped amorphous SilnZnO thin-film transistors. Solid-State Electronics, 2019, 158, 59-63.	1.4	5
11	Dependency of Si Content on the Performance of Amorphous SiZnSnO Thin Film Transistor Based Logic Circuits for Next-Generation Integrated Circuits. Transactions on Electrical and Electronic Materials, 2019, 20, 175-180.	1.9	6
12	Investigation on energy bandgap states of amorphous SiZnSnO thin films. Scientific Reports, 2019, 9, 19246.	3.3	15
13	Thin Film Logic Circuit with Metal Capping Layered amorphous SiZnSnO thin-film transistors. , 2018, , .		1
14	Direct investigation on energy bandgap of Si added ZnSnO system for stability enhancement by X-ray photoelectron spectroscopy. Journal of Alloys and Compounds, 2017, 715, 9-15.	5 . 5	22